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PROVIDING A SEMICONDUCTOR SUBSTRATE IN A CVD REACTOR ON A SUBSTRATE SUPPORT CAPABLE OF MAINTAINING THE SUBSTRATE AT A TEMPERATURE NOT EXCEEDING ABOUT 25°C DURING FORMATION OF FLUORINE AND CARBON-CONTAINING SILICON OXIDE DIELECTRIC MATERIAL

INTRODUCING INTO THE CVD REACTOR A VAPOROUS SOURCE OF PEROXIDE AND A VAPOROUS ORGANOFLUORO SILANE

DEPOSITING ON THE SUBSTRATE IN THE CVD REACTOR A LOW K FILM OF FLUORINE AND CARBON-CONTAINING SILICON OXIDE DIELECTRIC MATERIAL CHARACTERIZED BY IMPROVED RESISTANCE TO OXIDATION

FIGURE 1

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PROVIDING A SEMICONDUCTOR SUBSTRATE IN A CVD REACTOR ON A SUBSTRATE SUPPORT

INTRODUCING INTO THE CVD REACTOR A VAPOROUS SOURCE OF OZONE AND A VAPOROUS ORGANOFLUORO SILANE

DEPOSITING ON THE SUBSTRATE IN THE CVD REACTOR A LOW K FILM OF FLUORINE AND CARBON-CONTAINING SILICON OXIDE DIELECTRIC MATERIAL CHARACTERIZED BY IMPROVED RESISTANCE TO OXIDATION

FIGURE 2